

Trench gate field-stop IGBT, M series 650 V, 6 A low loss

Datasheet - production data

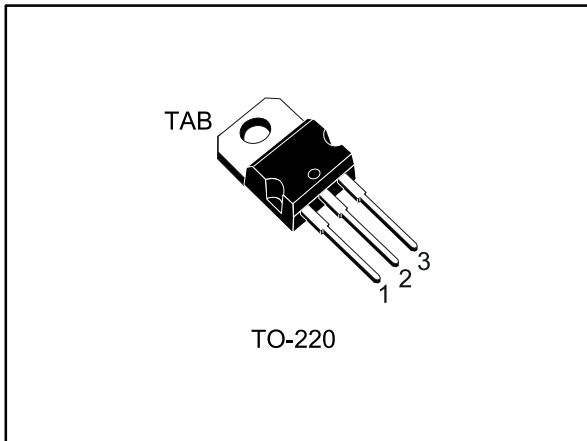
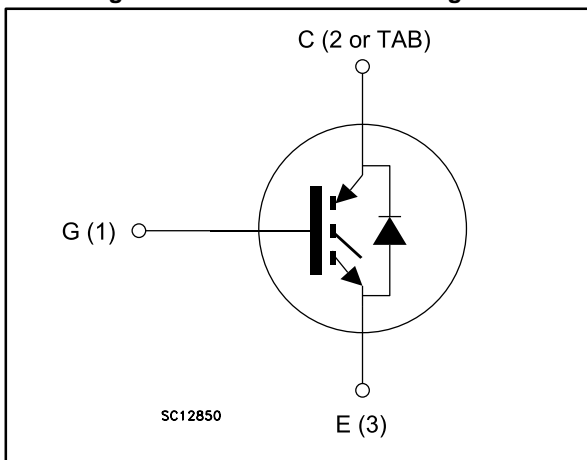


Figure 1: Internal schematic diagram



Features

- 6 μ s of short-circuit withstand time
- $V_{CE(sat)} = 1.55$ V (typ.) @ $I_c = 6$ A
- Tight parameter distribution
- Safer paralleling
- Low thermal resistance
- Soft and very fast recovery antiparallel diode

Applications

- Motor control
- UPS
- PFC

Description

This device is an IGBT developed using an advanced proprietary trench gate field-stop structure. The device is part of the M series IGBTs, which represent an optimal balance between inverter system performance and efficiency where low-loss and short-circuit functionality are essential. Furthermore, the positive $V_{CE(sat)}$ temperature coefficient and tight parameter distribution result in safer paralleling operation.

Table 1: Device summary

Order code	Marking	Package	Packing
STGP6M65DF2	G6M65DF2	TO-220	Tube

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1 Electrical ratings

Table 2: Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{CES}	Collector-emitter voltage ($V_{GE} = 0$ V)	650	V
I_C	Continuous collector current at $T_C = 25$ °C	12	A
	Continuous collector current at $T_C = 100$ °C	6	A
$I_{CP}^{(1)}$	Pulsed collector current	24	A
V_{GE}	Gate-emitter voltage	± 20	V
I_F	Continuous forward current at $T_C = 25$ °C	12	A
	Continuous forward current at $T_C = 100$ °C	6	A
$I_{FP}^{(1)}$	Pulsed forward current	24	A
P_{TOT}	Total dissipation at $T_C = 25$ °C	88	W
T_{STG}	Storage temperature range	- 55 to 150	°C
T_J	Operating junction temperature range	- 55 to 175	°C

Notes:

⁽¹⁾Pulse width limited by maximum junction temperature.

Table 3: Thermal data

Symbol	Parameter	Value	Unit
R_{thJC}	Thermal resistance junction-case IGBT	1.7	°C/W
R_{thJC}	Thermal resistance junction-case diode	5	°C/W
R_{thJA}	Thermal resistance junction-ambient	62.5	°C/W

2 Electrical characteristics

$T_C = 25\text{ °C}$ unless otherwise specified

Table 4: Static characteristics

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)CES}$	Collector-emitter breakdown voltage	$V_{GE} = 0\text{ V}$, $I_C = 250\text{ }\mu\text{A}$	650			V
$V_{CE(sat)}$	Collector-emitter saturation voltage	$V_{GE} = 15\text{ V}$, $I_C = 6\text{ A}$		1.55	2.0	V
		$V_{GE} = 15\text{ V}$, $I_C = 6\text{ A}$, $T_J = 125\text{ °C}$		1.9		
		$V_{GE} = 15\text{ V}$, $I_C = 6\text{ A}$, $T_J = 175\text{ °C}$		2.1		
V_F	Forward on-voltage	$I_F = 6\text{ A}$		2.2		V
		$I_F = 6\text{ A}$, $T_J = 125\text{ °C}$		2.0		
		$I_F = 6\text{ A}$, $T_J = 175\text{ °C}$		1.9		
$V_{GE(th)}$	Gate threshold voltage	$V_{CE} = V_{GE}$, $I_C = 250\text{ }\mu\text{A}$	5	6	7	V
I_{CES}	Collector cut-off current	$V_{GE} = 0\text{ V}$, $V_{CE} = 650\text{ V}$			25	μA
I_{GES}	Gate-emitter leakage current	$V_{CE} = 0\text{ V}$, $V_{GE} = \pm 20\text{ V}$			± 250	μA

Table 5: Dynamic characteristics

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{ies}	Input capacitance	$V_{CE} = 25\text{ V}$, $f = 1\text{ MHz}$, $V_{GE} = 0\text{ V}$	-	530	-	pF
C_{oes}	Output capacitance		-	31	-	
C_{res}	Reverse transfer capacitance		-	11	-	
Q_g	Total gate charge	$V_{CC} = 520\text{ V}$, $I_C = 6\text{ A}$, $V_{GE} = 15\text{ V}$ (see Figure 30: "Gate charge test circuit")	-	21.2	-	nC
Q_{ge}	Gate-emitter charge		-	5.2	-	
Q_{gc}	Gate-collector charge		-	8.8	-	

Table 6: IGBT switching characteristics (inductive load)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{CE} = 400 \text{ V}$, $I_C = 6 \text{ A}$, $V_{GE} = 15 \text{ V}$, $R_G = 22 \Omega$ (see Figure 29: "Test circuit for inductive load switching")		15	-	ns
t_r	Current rise time			5.8	-	ns
$(di/dt)_{on}$	Turn-on current slope			828	-	A/ μ s
$t_{d(off)}$	Turn-off-delay time			90	-	ns
t_f	Current fall time			130	-	ns
$E_{on(1)}$	Turn-on switching energy			0.036	-	mJ
$E_{off(2)}$	Turn-off switching energy			0.200	-	mJ
E_{ts}	Total switching energy			0.236	-	mJ
$t_{d(on)}$	Turn-on delay time	$V_{CE} = 400 \text{ V}$, $I_C = 6 \text{ A}$, $V_{GE} = 15 \text{ V}$, $R_G = 22 \Omega$, $T_J = 175 \text{ }^\circ\text{C}$ (see Figure 29: "Test circuit for inductive load switching")		17	-	ns
t_r	Current rise time			7	-	ns
$(di/dt)_{on}$	Turn-on current slope			685	-	A/ μ s
$t_{d(off)}$	Turn-off-delay time			86	-	ns
t_f	Current fall time			205	-	ns
$E_{on(1)}$	Turn-on switching energy			0.064	-	mJ
$E_{off(2)}$	Turn-off switching energy			0.290	-	mJ
E_{ts}	Total switching energy			0.354	-	mJ
t_{sc}	Short-circuit withstand time	$V_{CC} \leq 400 \text{ V}$, $V_{GE} = 15 \text{ V}$, $T_{Jstart} = 150 \text{ }^\circ\text{C}$	6		-	μ s
		$V_{CC} \leq 400 \text{ V}$, $V_{GE} = 13 \text{ V}$, $T_{Jstart} = 150 \text{ }^\circ\text{C}$	10		-	μ s

Notes:

(1) Turn-on switching energy includes reverse recovery of the diode.

(2) Turn-off switching energy also includes the tail of the collector current.

Table 7: Diode switching characteristics (inductive load)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
t_{rr}	Reverse recovery time	$I_F = 6\text{ A}$, $V_R = 400\text{ V}$, $V_{GE} = 15\text{ V}$ (see Figure 29: "Test circuit for inductive load switching") $di/dt = 1000\text{ A}/\mu\text{s}$	-	140		ns
Q_{rr}	Reverse recovery charge		-	210		nC
I_{rrm}	Reverse recovery current		-	6.6		A
dl_{rr}/dt	Peak rate of fall of reverse recovery current during t_b		-	430		A/ μs
E_{rr}	Reverse recovery energy		-	16		μJ
t_{rr}	Reverse recovery time	$I_F = 6\text{ A}$, $V_R = 400\text{ V}$, $V_{GE} = 15\text{ V}$ $T_J = 175\text{ }^\circ\text{C}$ (see Figure 29: "Test circuit for inductive load switching") $di/dt = 1000\text{ A}/\mu\text{s}$	-	200		ns
Q_{rr}	Reverse recovery charge		-	473		nC
I_{rrm}	Reverse recovery current		-	9.6		A
dl_{rr}/dt	Peak rate of fall of reverse recovery current during t_b		-	428		A/ μs
E_{rr}	Reverse recovery energy		-	32		μJ

2.1 Electrical characteristics (curves)

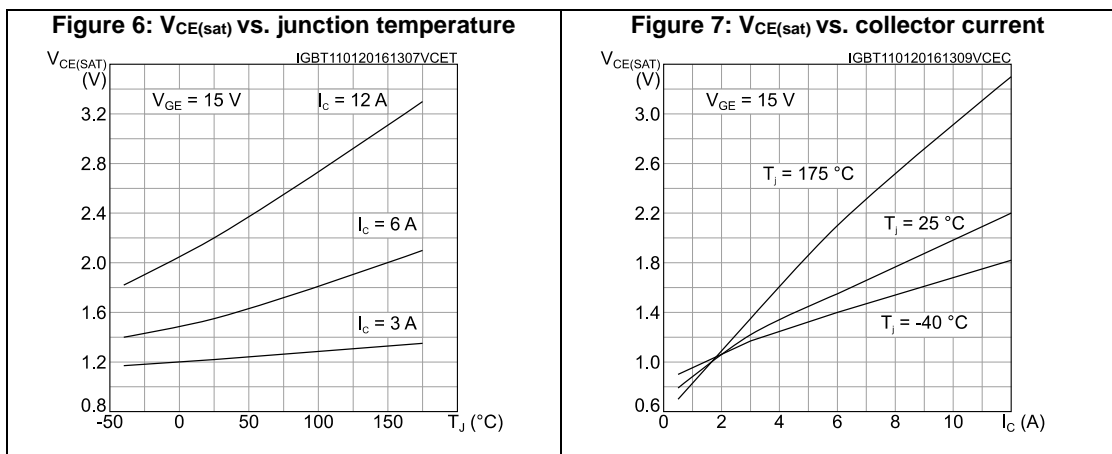
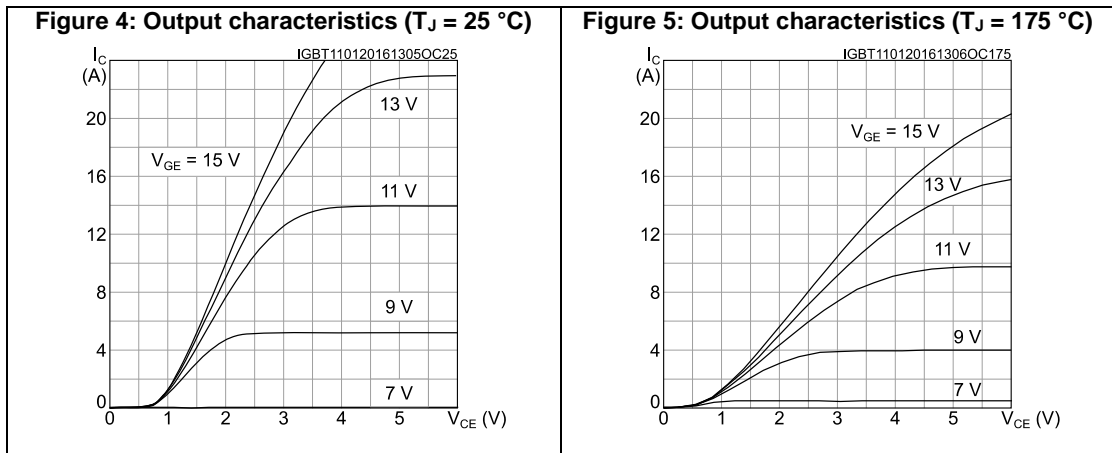
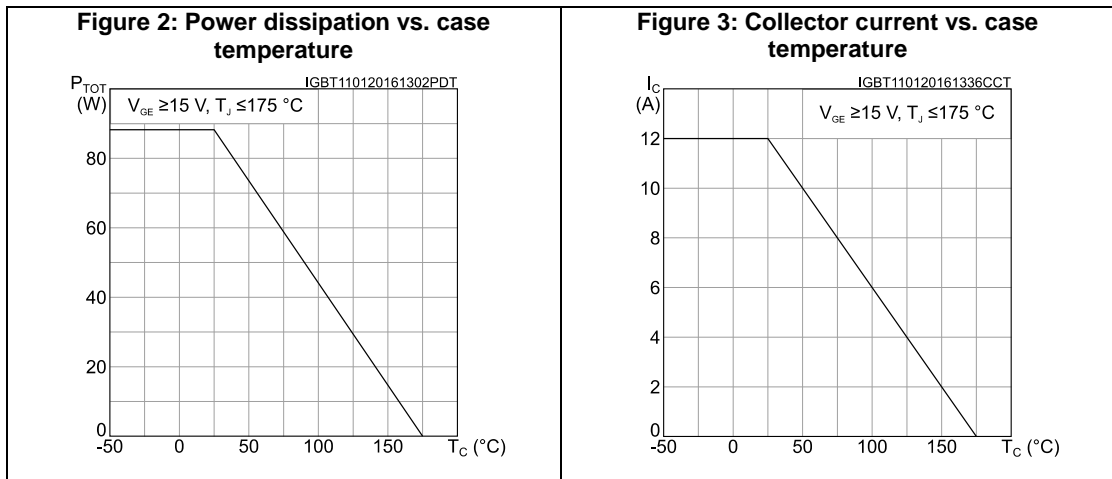


Figure 8: Collector current vs. switching frequency

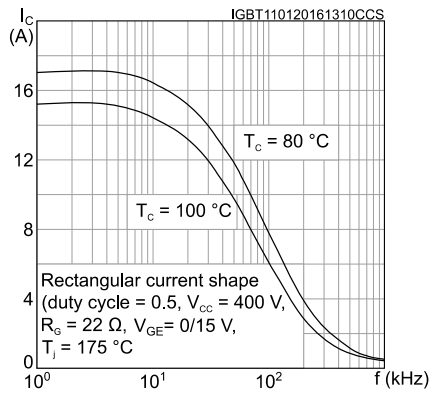


Figure 9: Forward bias safe operating area

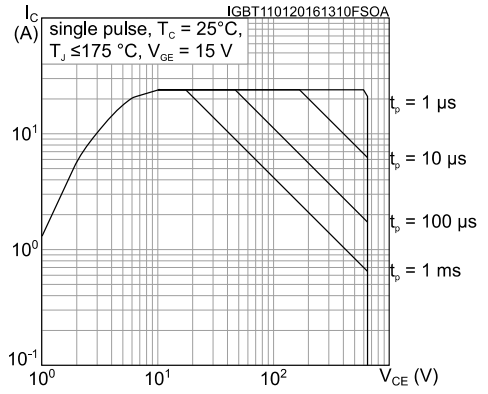


Figure 10: Transfer characteristics

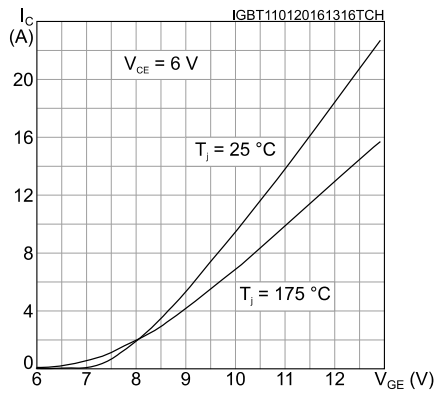


Figure 11: Diode V_F vs. forward current

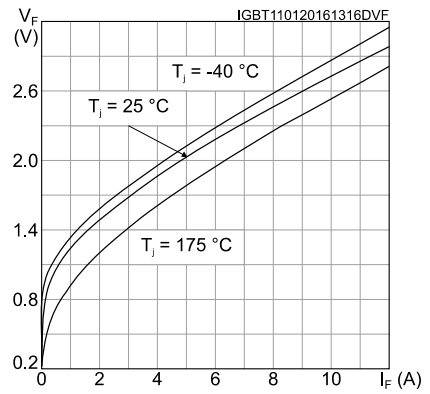


Figure 12: Normalized V_GE(th) vs. junction temperature

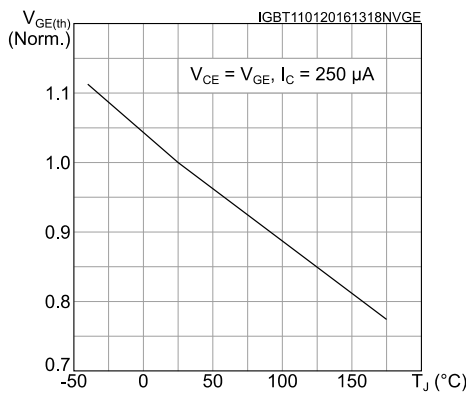
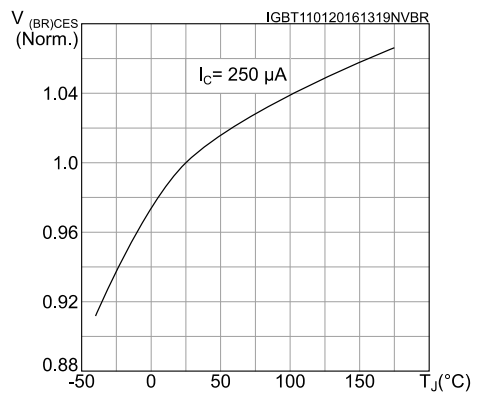


Figure 13: Normalized V_(BR)CES vs. junction temperature



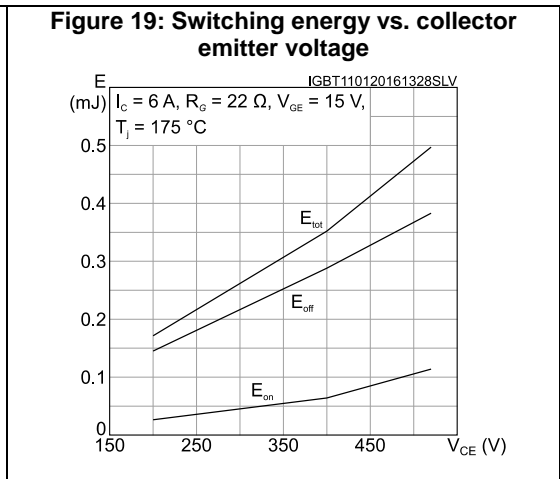
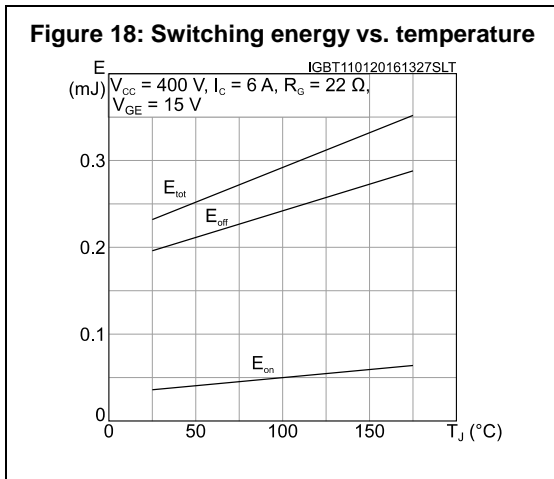
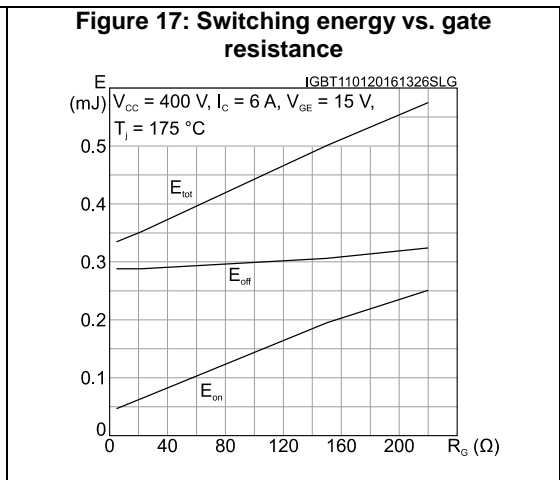
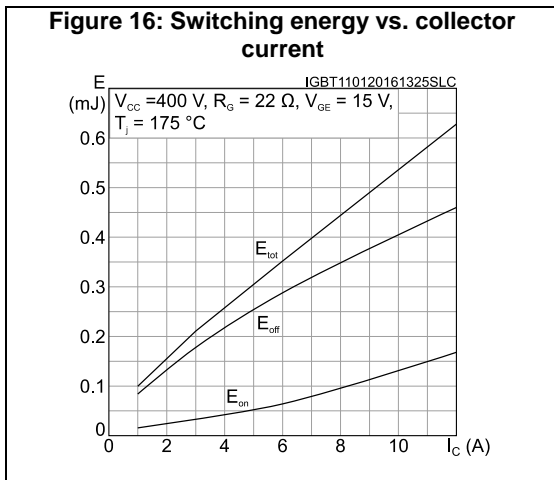
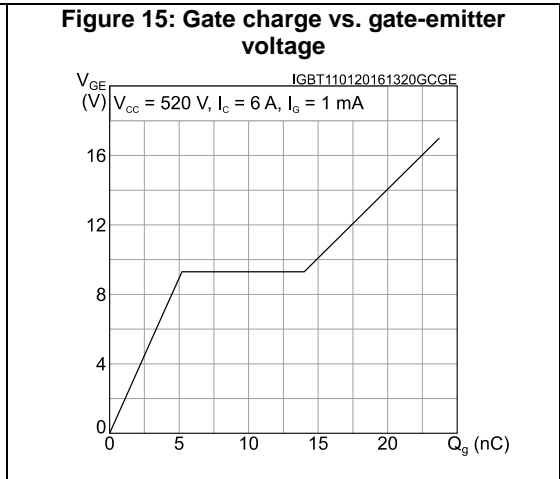
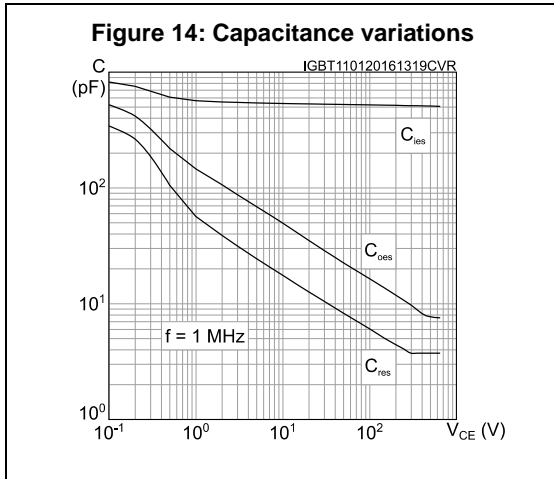


Figure 20: Short-circuit time and current vs. V_{GE}

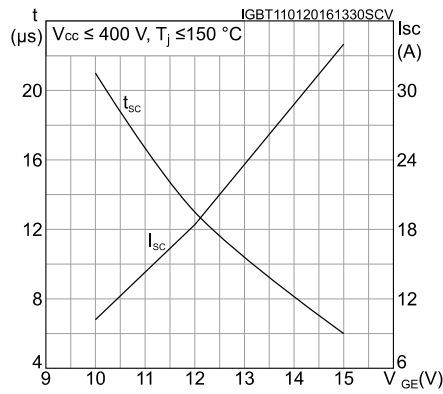


Figure 21: Switching times vs. collector current

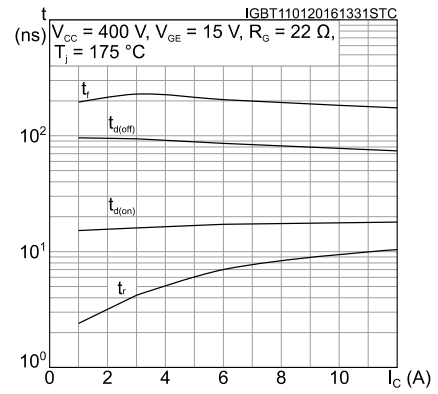


Figure 22: Switching times vs. gate resistance

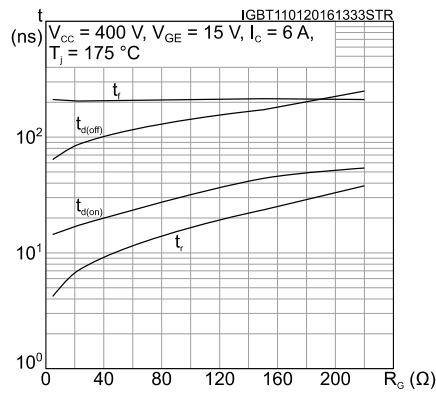


Figure 23: Reverse recovery current vs. diode current slope

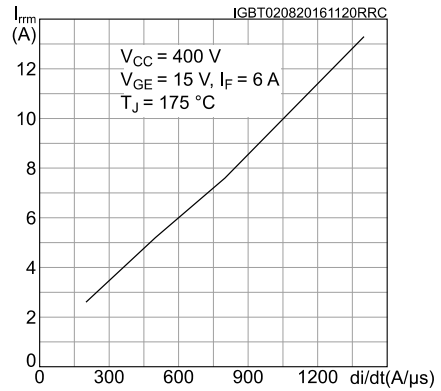


Figure 24: Reverse recovery time vs. diode current slope

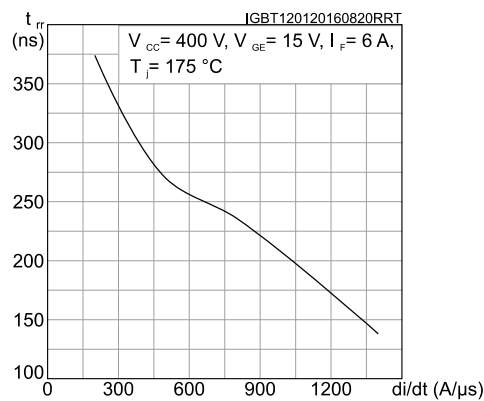


Figure 25: Reverse recovery charge vs. diode current slope

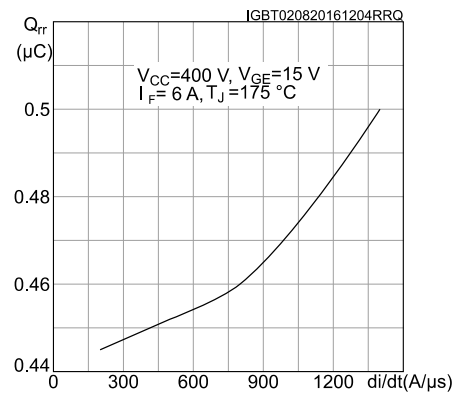


Figure 26: Reverse recovery energy vs. diode current slope

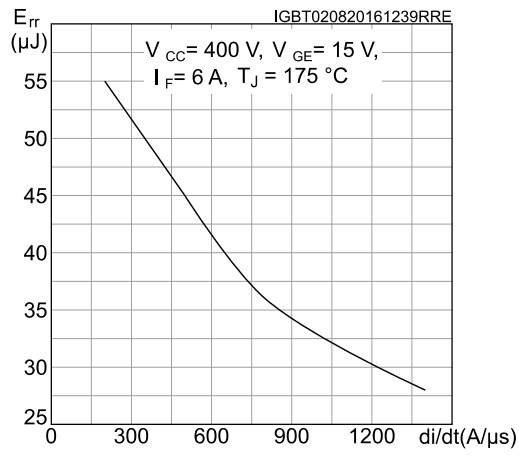


Figure 27: Thermal impedance for IGBT

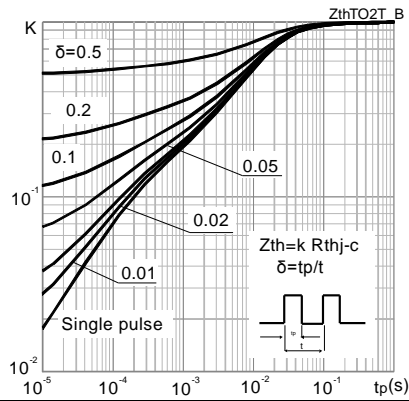
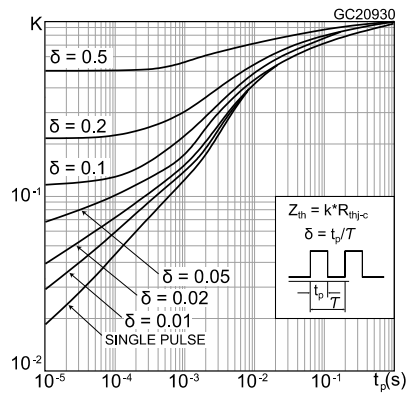


Figure 28: Thermal impedance for diode



4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK® is an ST trademark.

4.1 TO-220 type A package information

Figure 33: TO-220 type A package outline

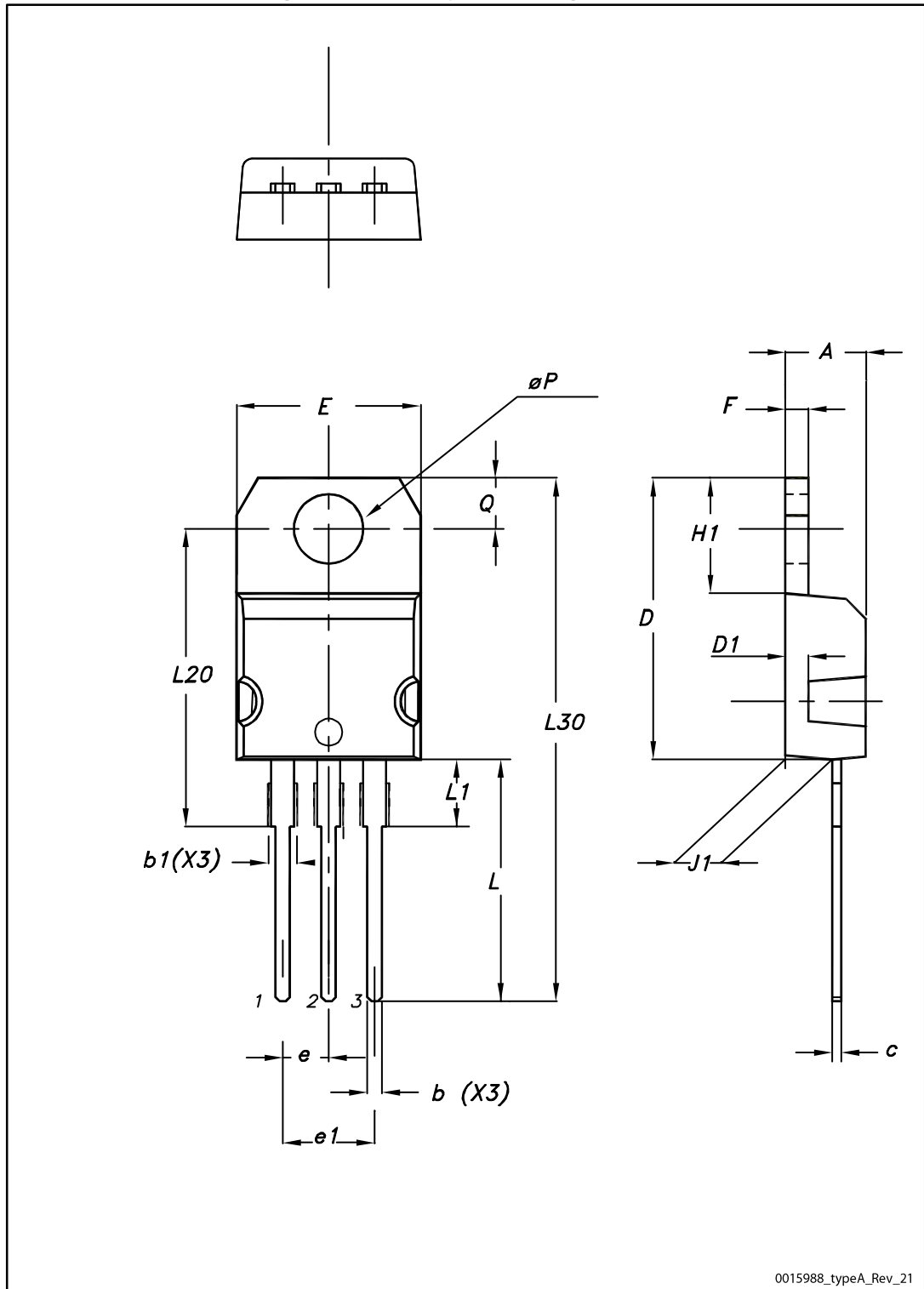


Table 8: TO-220 type A mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
b	0.61		0.88
b1	1.14		1.55
c	0.48		0.70
D	15.25		15.75
D1		1.27	
E	10.00		10.40
e	2.40		2.70
e1	4.95		5.15
F	1.23		1.32
H1	6.20		6.60
J1	2.40		2.72
L	13.00		14.00
L1	3.50		3.93
L20		16.40	
L30		28.90	
øP	3.75		3.85
Q	2.65		2.95

5 Revision history

Table 9: Document revision history

Date	Revision	Changes
30-Nov-2015	1	First release.
13-Jan-2016	2	Modified: <i>Table 4: "Static characteristics"</i> , <i>Table 5: "Dynamic characteristics"</i> , <i>Table 6: "IGBT switching characteristics (inductive load)"</i> , and <i>Table 7: "Diode switching characteristics (inductive load)"</i> Added: <i>Section 2.1: "Electrical characteristics (curves)"</i> Minor text changes.
03-Aug-2016	3	Updated <i>Table 2: "Absolute maximum ratings"</i> , <i>Table 4: "Static characteristics"</i> , <i>Table 6: "IGBT switching characteristics (inductive load)"</i> , <i>Table 7: "Diode switching characteristics (inductive load)"</i> . Updated <i>Figure 9: "Forward bias safe operating area"</i> , <i>Figure 12: "Normalized VGE(th) vs. junction temperature"</i> , <i>Figure 20: "Short-circuit time and current vs. VGE"</i> , <i>Figure 23: "Reverse recovery current vs. diode current slope"</i> . Changed <i>Figure 25: "Reverse recovery charge vs. diode current slope"</i> and <i>Figure 26: "Reverse recovery energy vs. diode current slope"</i> .

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